2-Mbit (256K x 8) MoBL® Static RAM

Features

- **Very high speed: 45 ns**
  - **Wide voltage range: 2.20V – 3.60V**
- **Pin-compatible with CY62138CV30**
- **Ultra-low standby power**
  - **Typical standby current: 1 µA**
  - **Maximum standby current: 7 µA**
- **Ultra-low active power**
  - **Typical active current: 2 mA @ f = 1 MHz**
- **Easy memory expansion with CE and OE features**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Offered in Pb-free 36-ball BGA package**

Functional Description[1]

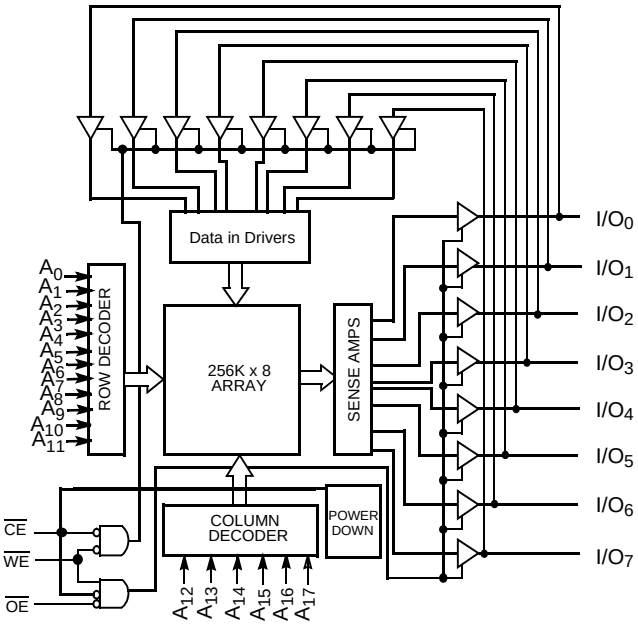
The CY62138EV30 is a high-performance CMOS static RAM organized as 256K words by 8 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life™ (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that significantly reduces power consumption. The device can be put into standby mode reducing power consumption when deselected (CE HIGH).

Writing to the device is accomplished by taking Chip Enable (CE) and Write Enable (WE) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{18}).

Reading from the device is accomplished by taking Chip Enable (CE) and Output Enable (OE) LOW while forcing Write Enable (WE) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (CE HIGH), the outputs are disabled (OE HIGH), or during a write operation (CE LOW and WE LOW).

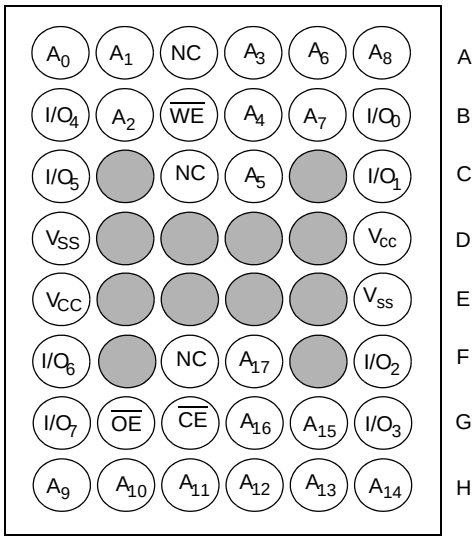
Logic Block Diagram



Note:
1. For best practice recommendations, please refer to the Cypress application note “System Design Guidelines” on http://www.cypress.com.

Pin Configuration[2]

FBGA
Top View



Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation					
					Operating I_{CC} (mA)				Standby I_{SB2} (µA)	
					f = 1 MHz		f = f_{max}			
	Min.	Typ.[3]	Max.		Typ.[3]	Max.	Typ.[3]	Max.	Typ.[3]	Max.
CY62138EV30LL	2.2	3.0	3.6	45	2	2.5	15	20	1	7

Notes:
2. NC pins are not connected on the die.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at $V_{CC} = V_{CC(typ.)}$, $T_A = 25°C$.

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied ..... 55°C to +125°C

Supply Voltage to Ground Potential ..... –0.3V to $V_{CC(MAX)}$ + 0.3V

DC Voltage Applied to Outputs in High-Z State[4,5] ..... –0.3V to $V_{CC(MAX)}$ + 0.3V

DC Input Voltage[4,5] ..... –0.3V to $V_{CC(MAX)}$ + 0.3V

Output Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage ..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... > 200 mA

Product	Range	Ambient Temperature	V_{CC}[6]
CY62138EV30LL	Industrial	–40°C to +85°C	2.2V to 3.6V

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62138EV30-45 Min.	Typ.[3]	Max.	Unit
V_{OH}	Output HIGH Voltage	I_{OH} = –0.1 mA	V_{CC} = 2.20V	2.0			V
		I_{OH} = –1.0 mA	V_{CC} = 2.70V	2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 0.1 mA	V_{CC} = 2.20V			0.4	V
		I_{OL} = 2.1 mA	V_{CC} = 2.70V			0.4	V
V_{IH}	Input HIGH Voltage	V_{CC} = 2.2V to 2.7V		1.8		V_{CC} + 0.3V	V
		V_{CC}= 2.7V to 3.6V		2.2		V_{CC} + 0.3V	V
V_{IL}	Input LOW Voltage	V_{CC} = 2.2V to 2.7V		–0.3		0.6	V
		V_{CC}= 2.7V to 3.6V		–0.3		0.8	V
I_{IX}	Input Leakage Current	GND ≤ V_I ≤ V_{CC}		–1		+1	µA
I_{OZ}	Output Leakage Current	GND ≤ V_O ≤ V_{CC}, Output Disabled		–1		+1	µA
I_{CC}	V_{CC} Operating Supply Current	f = f_{MAX} = $1/t_{RC}$	V_{CC} = V_{CCmax} I_{OUT} = 0 mA CMOS levels		15	20	mA
		f = 1 MHz			2	2.5	mA
I_{SB1}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V, V_{IN} ≤ 0.2V), f = f_{MAX} (Address and Data Only), f = 0 ($\overline{OE}$, and $\overline{WE}$), V_{CC} = 3.60V			1	7	µA
I_{SB2}	Automatic CE Power-down Current — CMOS Inputs	$\overline{CE}$ ≥ V_{CC} – 0.2V, V_{IN} ≥ V_{CC} – 0.2V or V_{IN} ≤ 0.2V, f = 0, V_{CC} = 3.60V			1	7	µA

Capacitance for all packages[7]

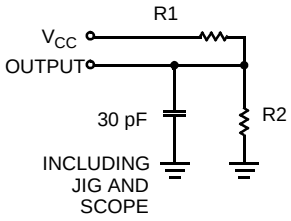
Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{CC} = $V_{CC(typ.)}$	10	pF
C_{OUT}	Output Capacitance		10	pF

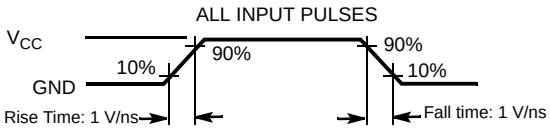
Notes:
4. $V_{IL(min.)}$ = –2.0V for pulse durations less than 20 ns.
5. $V_{IH(max)}$ = V_{CC}+0.75V for pulse durations less than 20 ns.
6. Full device AC operation assumes a 100 µs ramp time from 0 to V_{CC}(min.) and 200 µs wait time after V_{CC} stabilization.

Thermal Resistance

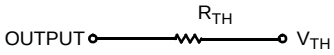
Parameter	Description	Test Conditions	BGA	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Still Air, soldered on a 3 x 4.5 inch, four-layer printed circuit board	72	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		8.86	°C/W

AC Test Loads and Waveforms





Equivalent to: THÉVENIN EQUIVALENT

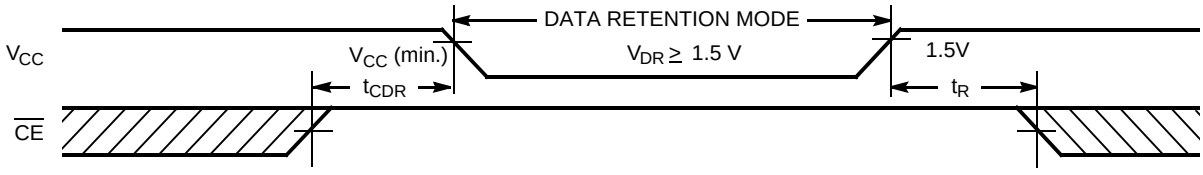


Parameters	2.50V	3.0V	Unit
R1	16667	1103	Ω
R2	15385	1554	Ω
R_{TH}	8000	645	Ω
V_{TH}	1.20	1.75	V

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions	Min.	Typ.[3]	Max.	Unit
V_{DR}	V_{CC} for Data Retention		1			V
I_{CCDR}	Data Retention Current	V_{CC} = 1V, $\overline{CE} \geq V_{CC} - 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$		0.8	3	µA
t_{CDR}[7]	Chip Deselect to Data Retention Time		0			ns
t_R[8]	Operation Recovery Time		t_{RC}			ns

Data Retention Waveform



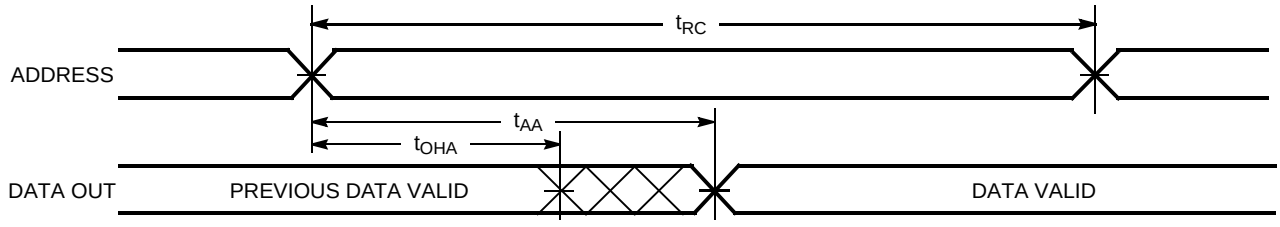
Notes:
7. Tested initially and after any design or process changes that may affect these parameters.
8. Full Device AC operation requires linear V_{CC} ramp from V_{DR} to $V_{CC(min.)} \geq 100$ µs or stable at $V_{CC(min.)} \geq 100$ µs.

Switching Characteristics (Over the Operating Range)[9]

Parameter	Description	45 ns		Unit
		Min.	Max.	
Read Cycle				
t_{RC}	Read Cycle Time	45		ns
t_{AA}	Address to Data Valid		45	ns
t_{OHA}	Data Hold from Address Change	10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		45	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		22	ns
t_{LZOE}	$\overline{OE}$ LOW to Low Z[10]	5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High Z[10,11]		18	ns
t_{LZCE}	$\overline{CE}$ LOW to Low Z[10]	10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High Z[10, 11]		18	ns
t_{PU}	$\overline{CE}$ LOW to Power-up	0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-up		45	ns
Write Cycle[12]				
t_{WC}	Write Cycle Time	45		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	35		ns
t_{AW}	Address Set-up to Write End	35		ns
t_{HA}	Address Hold from Write End	0		ns
t_{SA}	Address Set-up to Write Start	0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	35		ns
t_{SD}	Data Set-up to Write End	25		ns
t_{HD}	Data Hold from Write End	0		ns
t_{HZWE}	$\overline{WE}$ LOW to High Z[10, 11]		18	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low Z[10]	10		ns

Switching Waveforms

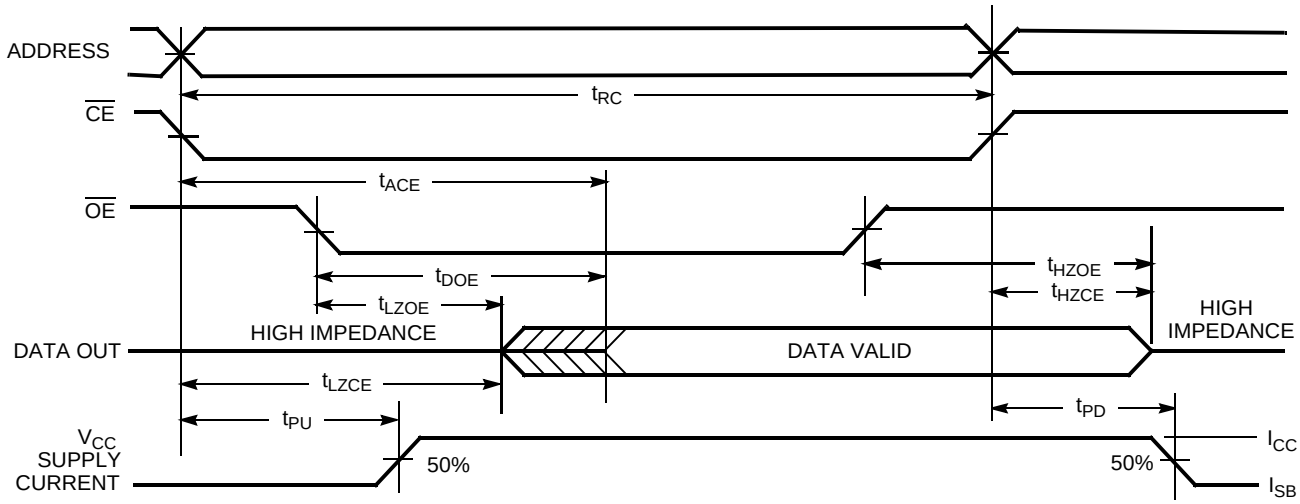
Read Cycle No. 1 (Address Transition Controlled)[13, 14]



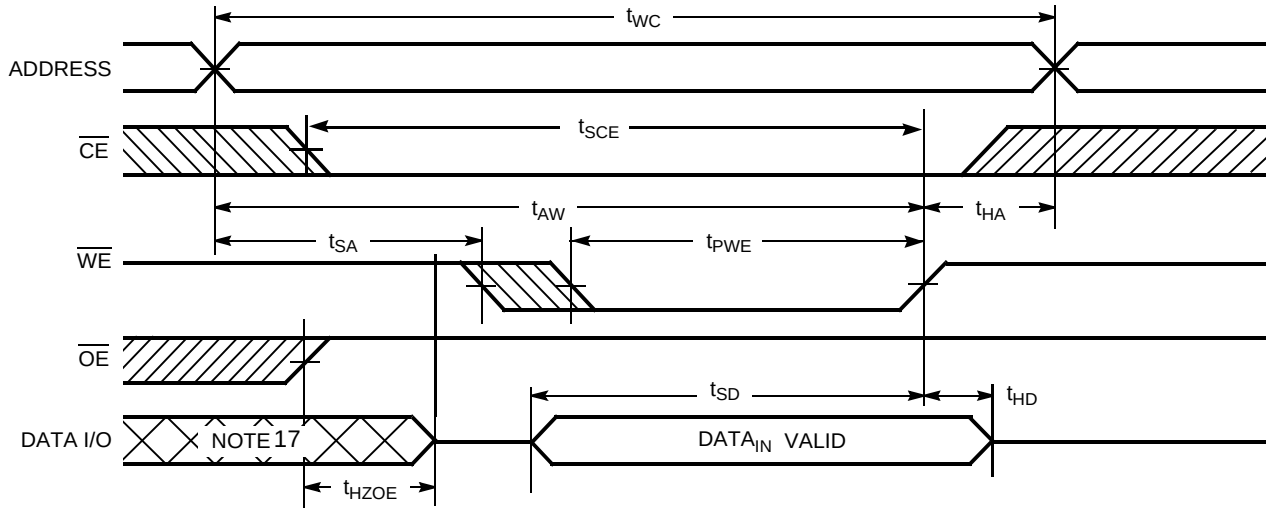
Notes:
9. Test Conditions for all parameters other than three-state parameters assume signal transition time of 3 ns or less (1 V/ns), timing reference levels of $V_{CC(typ)}/2$, input pulse levels of 0 to $V_{CC(typ)}$, and output loading of the specified I_{OL}/I_{OH} as shown in the “AC Test Loads and Waveforms” section.
10. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
11. t_{HZOE}, t_{HZCE}, and t_{HZWE} transitions are measured when the output enter a high-impedance state.
12. The internal write time of the memory is defined by the overlap of $\overline{WE}$, $\overline{CE}$ = V_{IL}. All signals must be ACTIVE to initiate a write and any of these signals can terminate a write by going INACTIVE. The data input set-up and hold timing should be referenced to the edge of the signal that terminates the write.
13. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
14. $\overline{WE}$ is HIGH for read cycle.

Switching Waveforms (continued)

Read Cycle No. 2 ($\overline{OE}$ Controlled)[14, 15]



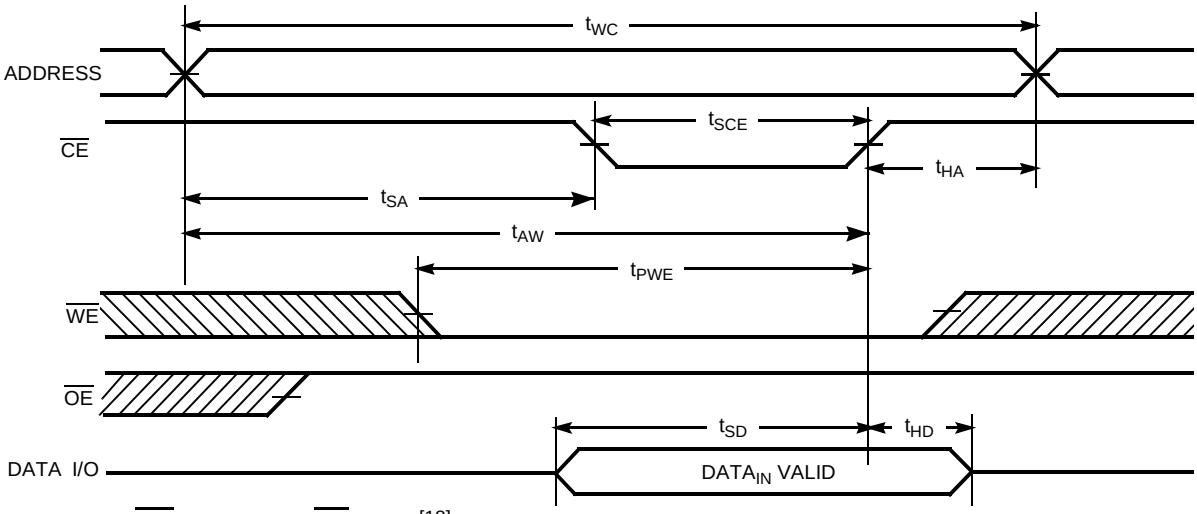
Write Cycle No. 1 ($\overline{WE}$ Controlled)[16, 18]



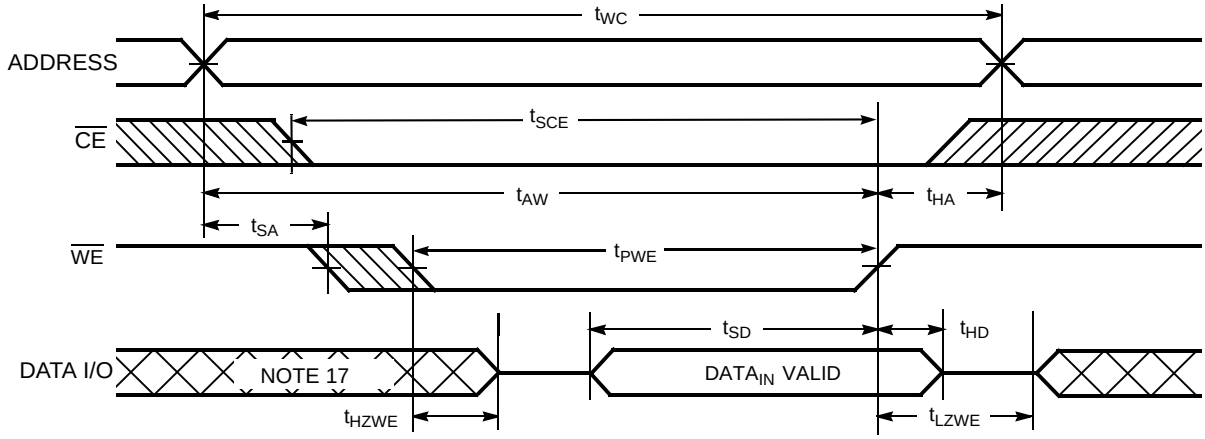
Notes:
15. Address valid prior to or coincident with $\overline{CE}$ transition LOW.
16. Data I/O is high impedance if $\overline{OE}$ = V_{IH}.
17. During this period, the I/Os are in output state and input signals should not be applied.
18. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in high-impedance state.

Switching Waveforms (continued)

Write Cycle No. 2 ($\overline{CE}$ Controlled)[16, 18]



Write Cycle No. 3 ($\overline{WE}$ Controlled, $\overline{OE}$ LOW)[18]



Truth Table

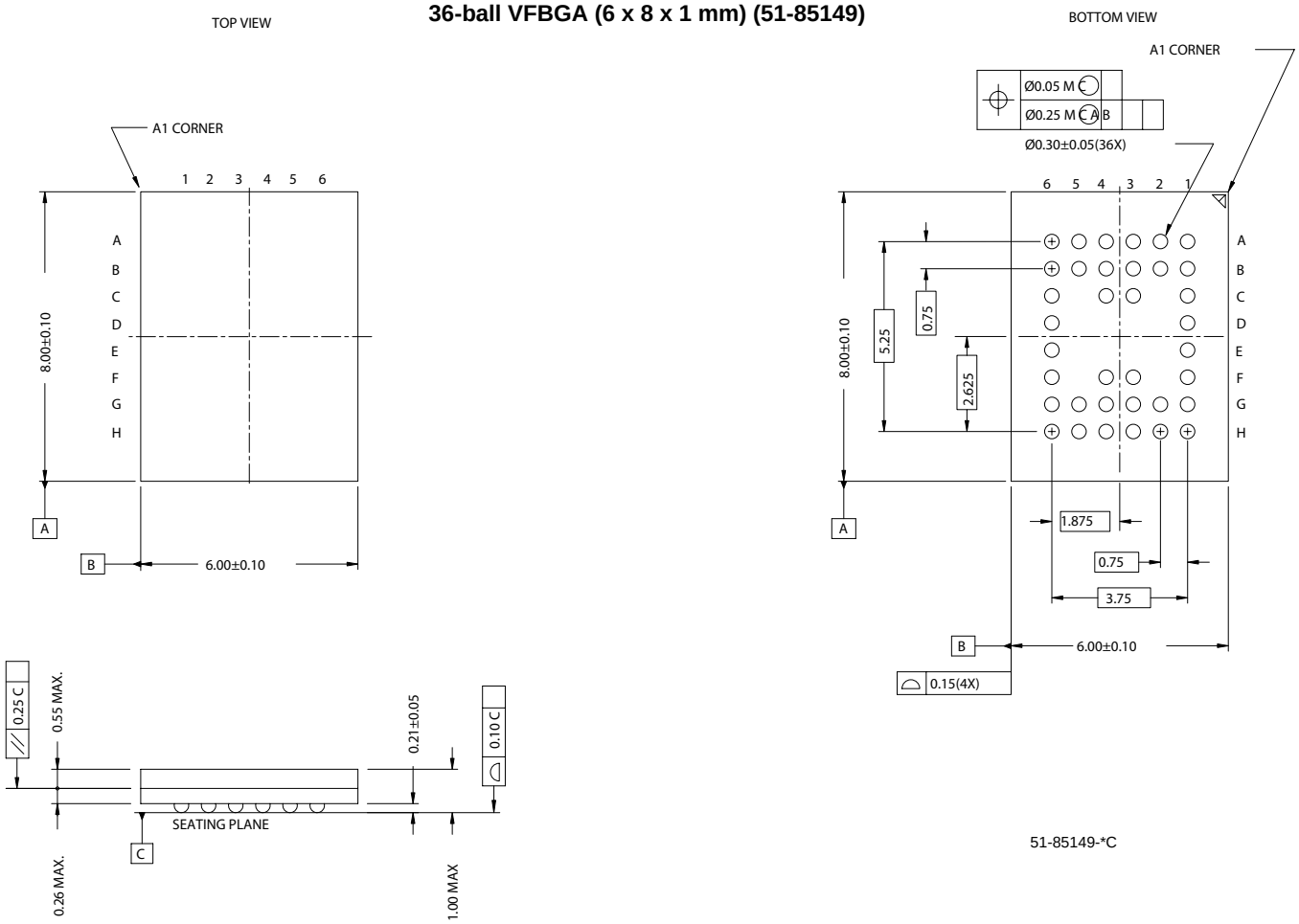
$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	Inputs/Outputs	Mode	Power
H	X	X	High Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	Data Out (I/O_0–I/O_7)	Read	Active (I_{CC})
L	H	H	High Z	Output Disabled	Active (I_{CC})
L	L	X	Data in (I/O_0–I/O_7)	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
45	CY62138EV30LL-45BVXI	51-85149	36-ball Very Fine Pitch BGA (6 mm × 8 mm × 1 mm) (Pb-free)	Industrial

Package Diagrams

36-ball VFBGA (6 x 8 x 1 mm) (51-85149)



Document History Page

Document Title: CY62138EV30 2-Mbit (256K x 8) MoBL® Static RAM Document Number: 38-05577				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	237432	See ECN	AJU	New data sheet
*A	427817	See ECN	NXR	Removed 35 ns Speed Bin Removed “L” version Removed 32-pin TSOPII package from product Offering. Changed ball C3 from DNU to NC. Removed the redundant footnote on DNU. Moved Product Portfolio from Page # 3 to Page #2. Changed I_{CC} (Max) value from 2 mA to 2.5 mA and I_{CC} (Typ) value from 1.5 mA to 2 mA at f = 1 MHz Changed I_{CC} (Typ) value from 12 mA to 15 mA at f = f_{max}=1/t_{RC} Changed I_{SB1} and I_{SB2} Typ. values from 0.7 μA to 1 μA and Max. values from 2.5 μA to 7 μA. Changed V_{CC} stabilization time in footnote #7 from 100 μs to 200 μs Changed the AC test load capacitance from 50pF to 30pF on Page# 4 Changed V_{DR} from 1.5V to 1V on Page# 4. Changed I_{CCDR} from 1 μA to 3 μA in the Data Retention Characteristics table on Page # 4. Corected t_R in Data Retention Characteristics from 100 μs to t_{RC} ns Changed t_{OHA}, t_{LZCE}, t_{LZWE} from 6 ns to 10 ns Changed t_{HZOE}, t_{HZCE}, t_{HZWE} from 15 ns to 18 ns Changed t_{LZOE} from 3 ns to 5 ns Changed t_{SCE} and t_{AW} from 40 ns to 35 ns Changed t_{SD} from 20 ns to 25 ns Changed t_{PWE} from 25 ns to 35 ns Updated the Ordering Information table and replaced Package Name column with Package Diagram.